Low-power dual buffer Rev. 6 — 17 September 2015

Product data sheet

General description 1.

The 74AUP2G34 provides two low-power, low-voltage buffers.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I_{OFF}.

The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. **Features and benefits**

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - ◆ JESD8-12 (0.8 V to 1.3 V)
 - ◆ JESD8-11 (0.9 V to 1.65 V)
 - ◆ JESD8-7 (1.2 V to 1.95 V)
 - ◆ JESD8-5 (1.8 V to 2.7 V)
 - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; I_{CC} = 0.9 μA (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



3. Ordering information

Table 1. Ordering information

Type number	Package								
	Temperature range	Name	Description	Version					
74AUP2G34GW	–40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363					
74AUP2G34GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886					
74AUP2G34GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1 \times 0.5 mm	SOT891					
74AUP2G34GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115					
74AUP2G34GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 1.0 \times 1.0 \times 0.35 mm	SOT1202					
74AUP2G34GX	–40 °C to +125 °C	X2SON6	plastic thermal extremely thin small outline package; no leads; 6 terminals; body 1 \times 0.8 \times 0.35 mm	SOT1255					

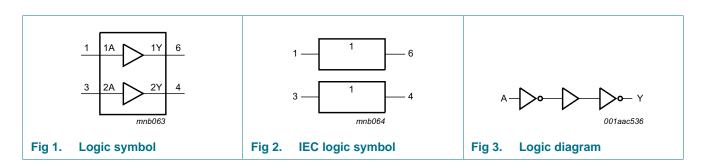
4. Marking

Table 2. Marking

Type number	Marking code ^[1]
74AUP2G34GW	аА
74AUP2G34GM	аА
74AUP2G34GF	аА
74AUP2G34GN	аА
74AUP2G34GS	аА
74AUP2G34GX	аА

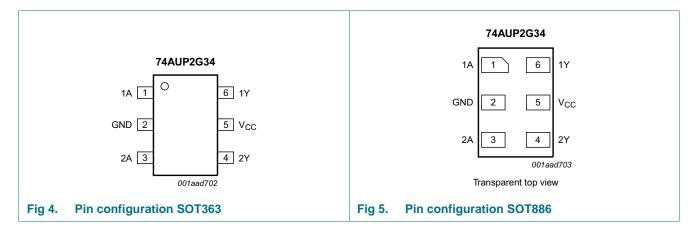
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information

6.1 Pinning





6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1A	1	data input
GND	2	ground (0 V)
2A	3	data input
2Y	4	data output
V _{CC}	5	supply voltage
1Y	6	data output

7. Functional description

Table 4. Function table[1]

Input	Output
nA	nY
L	L
Н	Н

^[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CC}	supply voltage			-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V		-50	-	mA
VI	input voltage		[1]	-0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V		-50	-	mA
Vo	output voltage	Active mode and Power-down mode	[1]	-0.5	+4.6	V
Io	output current	$V_O = 0 V \text{ to } V_{CC}$		-	±20	mA
I _{CC}	supply current			-	50	mA
I _{GND}	ground current			-50	-	mA
T _{stg}	storage temperature			-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	[2]	-	250	mW

^[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	V _{CC}	V
		Power-down mode; V _{CC} = 0 V	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 0.8 V to 3.6 V	-	200	ns/V

^[2] For SC-88 packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K. For X2SON6 and XSON6 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2	5 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	$0.70 \times V_{CC}$	-	-	V
		V _{CC} = 0.9 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V_{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	$0.30 \times V_{CC}$	V
		V _{CC} = 0.9 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_{O} = -20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	V _{CC} - 0.1	-	-	V
		$I_O = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.75 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.32	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	2.05	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.3 \times V_{CC}$	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.31	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.31	V
		$I_O = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
I _I	input leakage current	$V_{I} = GND \text{ to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.1	μΑ
I_{OFF}	power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.2	μΑ
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.2	μΑ
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 0.8 V to 3.6 V	-	-	0.5	μΑ
Δl _{CC}	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	40	μΑ
Cı	input capacitance	$V_{CC} = 0 \text{ V to } 3.6 \text{ V}; V_I = \text{GND or } V_{CC}$	-	8.0	-	pF
Co	output capacitance	$V_O = GND; V_{CC} = 0 V$	-	1.7	-	pF

 Table 7.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -	40 °C to +85 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	$0.70 \times V_{CC}$	-	-	V
		V _{CC} = 0.9 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	$0.30 \times V_{CC}$	V
		V _{CC} = 0.9 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_{O} = -20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	V _{CC} – 0.1	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.7 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.30	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.97	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.55	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.3 \times V_{CC}$	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.37	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.35	V
		$I_{O} = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.33	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.45	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.33	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.45	V
I _I	input leakage current	$V_{I} = GND \text{ to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.5	μΑ
I _{OFF}	power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.5	μΑ
ΔI_{OFF}	additional power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V	-	-	±0.6	μΑ
I _{CC}	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.9	μΑ
Δl _{CC}	additional supply current	$V_1 = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	-	-	50	μΑ

 Table 7.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -	40 °C to +125 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	$0.75 \times V_{CC}$	-	-	V
		V _{CC} = 0.9 V to 1.95 V	$0.70 \times V_{CC}$	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V_{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	$0.25 \times V_{CC}$	V
		V _{CC} = 0.9 V to 1.95 V	-	-	$0.30 \times V_{CC}$	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_{O} = -20 \mu A$; $V_{CC} = 0.8 \text{ V}$ to 3.6 V	V _{CC} – 0.11	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.6 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	0.93	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.17	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.77	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.67	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.40	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.30	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.11	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.33 \times V_{CC}$	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.41	V
		$I_{O} = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.39	V
		$I_{O} = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.36	V
		$I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
I _I	input leakage current	$V_{I} = GND \text{ to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.75	μΑ
I _{OFF}	power-off leakage current	V_{I} or $V_{O} = 0 \text{ V}$ to 3.6 V; $V_{CC} = 0 \text{ V}$	-	-	±0.75	μΑ
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.75	μΑ
I _{CC}	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μΑ
ΔI_{CC}	additional supply current	$V_1 = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	-	-	75	μА

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions		25 °C		-4	10 °C to +	125 °C	Unit
				Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 p	F						1		
t _{pd}	propagation delay	nA to nY; see Figure 8 [2]							
		V _{CC} = 0.8 V	-	14.9	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.6	4.7	9.2	2.0	10.0	11.0	ns
		V _{CC} = 1.4 V to 1.6 V	2.1	3.4	5.7	1.6	6.5	7.2	ns
		V _{CC} = 1.65 V to 1.95 V	1.8	2.9	4.5	1.4	5.2	5.8	ns
		V _{CC} = 2.3 V to 2.7 V	1.5	2.3	3.5	1.2	4.2	4.6	ns
		V _{CC} = 3.0 V to 3.6 V	1.4	2.1	3.2	1.0	3.8	4.2	ns
C _L = 10	pF								
t _{pd}	propagation delay	nA to nY; see Figure 8							
		V _{CC} = 0.8 V	-	18.4	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.2	5.6	10.9	2.3	11.8	13.1	ns
		V _{CC} = 1.4 V to 1.6 V	2.6	4.1	6.7	1.9	7.7	8.5	ns
		V _{CC} = 1.65 V to 1.95 V	2.3	3.4	5.3	1.7	6.2	6.9	ns
		V _{CC} = 2.3 V to 2.7 V	2.0	2.9	4.2	1.5	5.0	5.5	ns
		V _{CC} = 3.0 V to 3.6 V	1.7	2.6	3.8	1.4	4.6	5.1	ns
C _L = 15	pF								
t _{pd}	propagation delay	nA to nY; see Figure 8							
		V _{CC} = 0.8 V	-	21.9	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.6	6.4	12.6	2.6	13.8	15.2	ns
		V _{CC} = 1.4 V to 1.6 V	3.0	4.6	7.6	2.2	8.9	9.8	ns
		V _{CC} = 1.65 V to 1.95 V	2.6	3.9	6.0	2.0	7.2	7.9	ns
		V _{CC} = 2.3 V to 2.7 V	2.3	3.3	4.8	1.8	5.7	6.3	ns
		V _{CC} = 3.0 V to 3.6 V	2.1	3.1	4.2	1.6	5.0	5.5	ns
C _L = 30	pF								
t _{pd}	propagation delay	nA to nY; see Figure 8 [2]							
		V _{CC} = 0.8 V	-	32.1	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	4.8	8.7	16.3	3.6	18.9	20.8	ns
		V _{CC} = 1.4 V to 1.6 V	4.0	6.2	10.3	3.4	12.2	13.4	ns
		V _{CC} = 1.65 V to 1.95 V	3.6	5.2	8.1	3.2	9.8	10.8	ns
		V _{CC} = 2.3 V to 2.7 V	3.0	4.4	6.4	2.7	7.7	8.5	ns
		V _{CC} = 3.0 V to 3.6 V	2.9	4.2	5.6	2.5	6.5	7.2	ns

 Table 8.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions	25 °C				-4	0 °C to +	125 °C	Unit
				Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)		
C _L = 5 pl	F, 10 pF, 15 pF and	30 pF			<u>'</u>					
C _{PD}	power dissipation	$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$ [3][4]								
	capacitance	V _{CC} = 0.8 V	-	2.5	-	-	-	-	pF	
		V _{CC} = 1.1 V to 1.3 V	-	2.6	-	-	-	-	pF	
		V _{CC} = 1.4 V to 1.6 V	-	2.7	-	-	-	-	pF	
		V _{CC} = 1.65 V to 1.95 V	-	2.9	-	-	-	-	pF	
		V _{CC} = 2.3 V to 2.7 V	-	3.4	-	-	-	-	pF	
		V _{CC} = 3.0 V to 3.6 V	-	4.0	-	-	-	-	pF	

- [1] All typical values are measured at nominal V_{CC}.
- [2] t_{pd} is the same as t_{PLH} and t_{PHL} .
- [3] All specified values are the average typical values over all stated loads.
- [4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz;

 f_0 = output frequency in MHz;

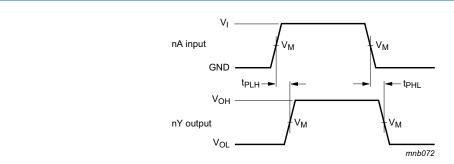
 C_L = load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms



Measurement points are given in Table 9.

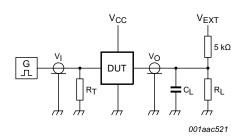
Logic levels: V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig 8. The data input (nA) to output (nY) propagation delays

Table 9. Measurement points

Supply voltage	Output	Input						
V _{CC}	V _M	V _M	VI	$t_r = t_f$				
0.8 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V _{CC}	≤ 3.0 ns				

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Test data is given in Table 10.

Definitions for test circuit:

R_L = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

 V_{EXT} = External voltage for measuring switching times.

Fig 9. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Load		V _{EXT}		
V _{CC}	CL	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times R_L = 5 $k\Omega$, for measuring propagation delays, setup and hold times and pulse width R_L = 1 $M\Omega$.

13. Package outline

SOT363 Plastic surface-mounted package; 6 leads Α X = v M A **-** ⊕ w M B detail X scale **DIMENSIONS** (mm are the original dimensions) A_1

OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT363			SC-88			-04-11-08- 06-03-16

ΗE

 $L_{\mathbf{p}}$

0.45

0.15

Q

0.25

0.15

٧

у

Fig 10. Package outline SOT363 (SC-88)

max

0.30

0.20

0.25 0.10

D

2.2 1.8

Е

1.35 1.15

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UNIT

Α

1.1

0.8

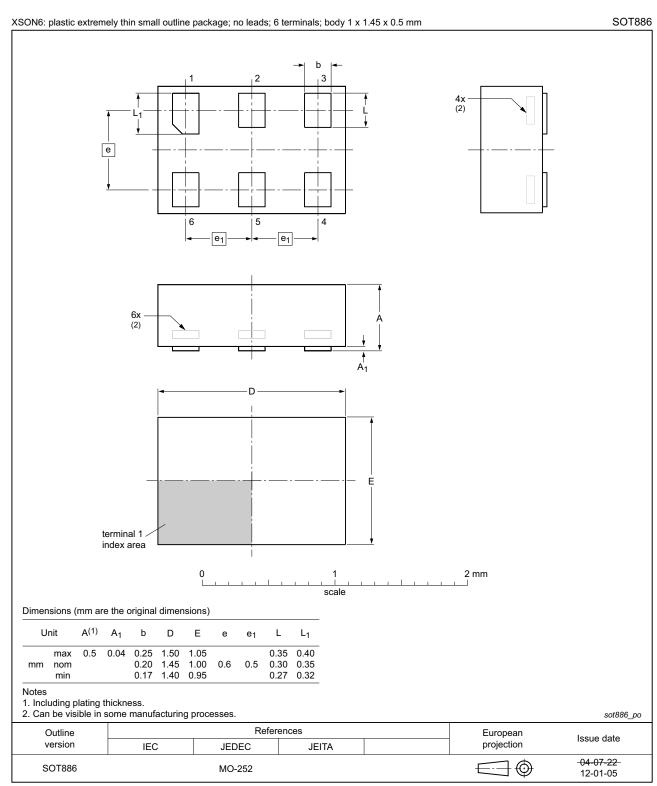


Fig 11. Package outline SOT886 (XSON6)

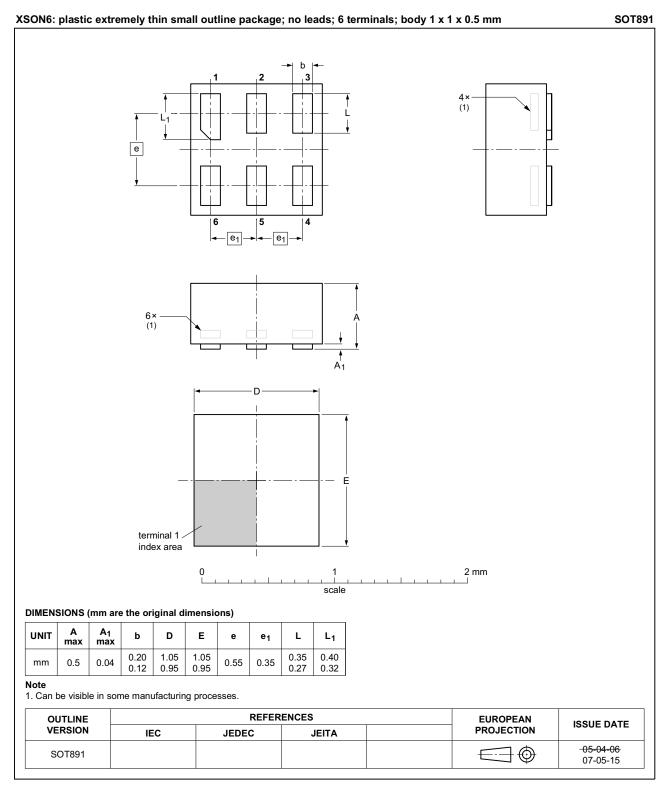


Fig 12. Package outline SOT891 (XSON6)

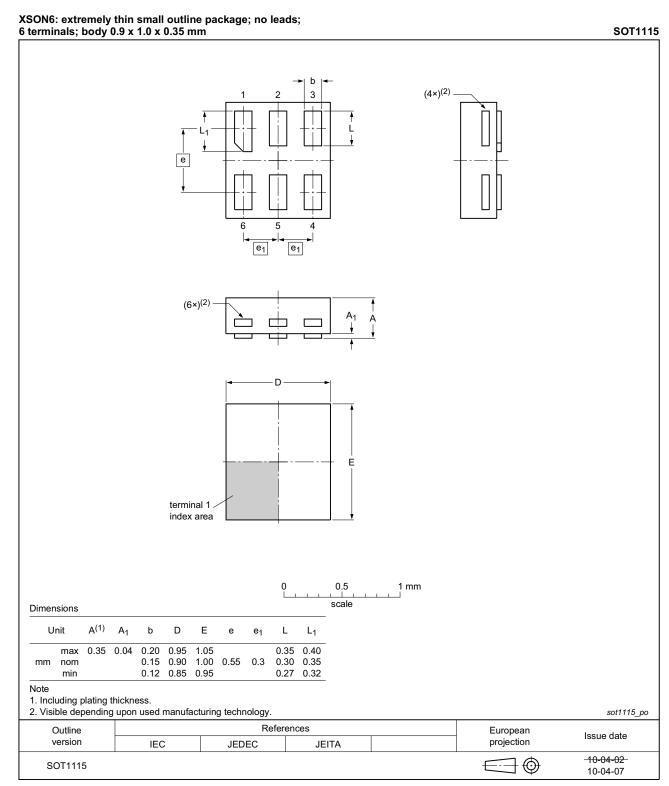


Fig 13. Package outline SOT1115 (XSON6)

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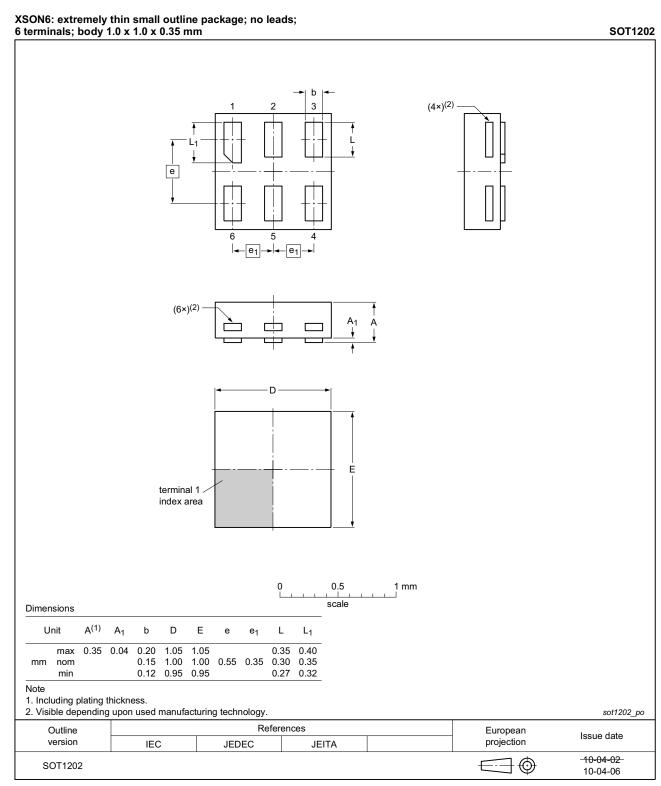


Fig 14. Package outline SOT1202 (XSON6)

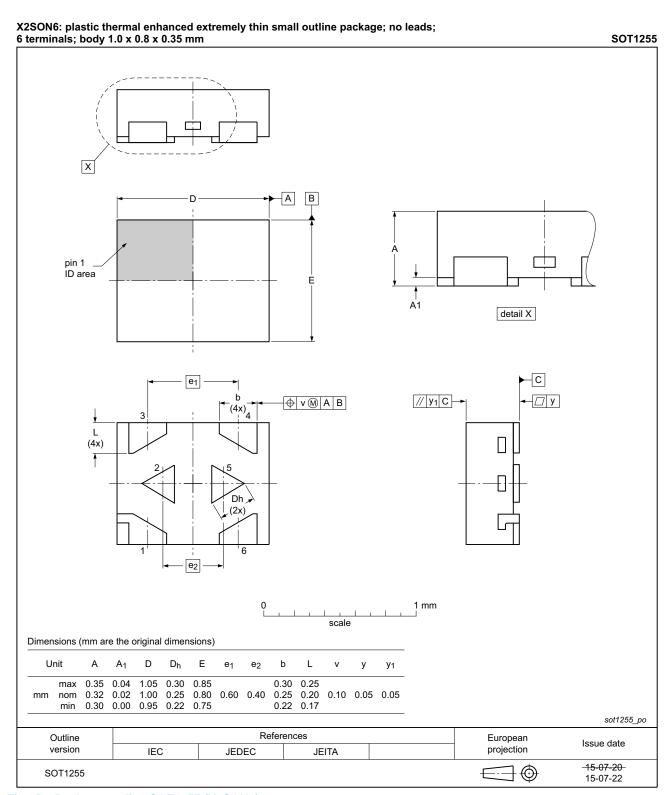


Fig 15. Package outline SOT1255 (X2SON6)

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP2G34 v.6	20150917	Product data sheet	-	74AUP2G34 v.5
Modifications:	Added type number 74AUP2G34GX (SOT1255/X2SON6).			
74AUP2G34 v.5	20130110	Product data sheet	-	74AUP2G34 v.4
Modifications:	Package outline drawing of SOT886 (Figure 11) modified.			
74AUP2G34 v.4	20111206	Product data sheet	-	74AUP2G34 v.3
Modifications:	Legal pages updated.			
74AUP2G34 v.3	20100903	Product data sheet	-	74AUP2G34 v.2
74AUP2G34 v.2	20080131	Product data sheet	-	74AUP2G34 v.1
74AUP2G34 v.1	20061122	Product data sheet	-	-

16. Legal information

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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